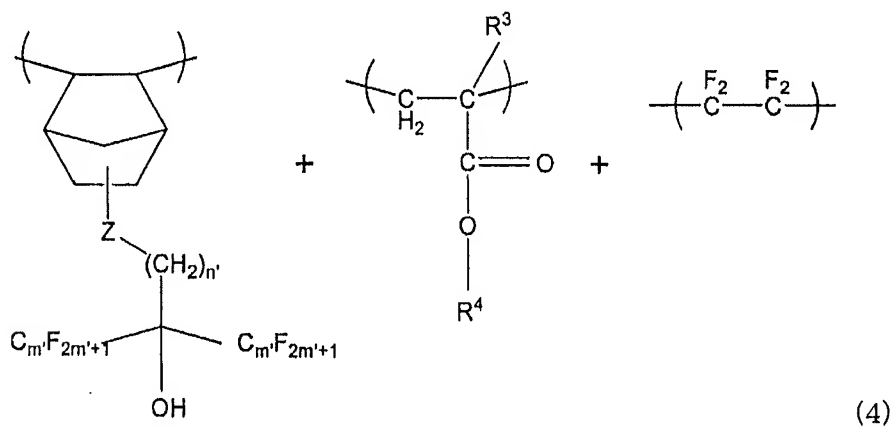
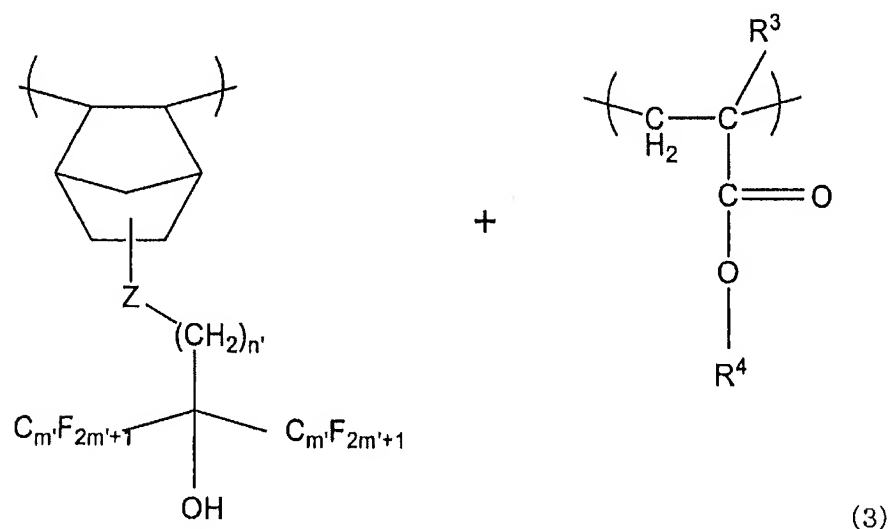
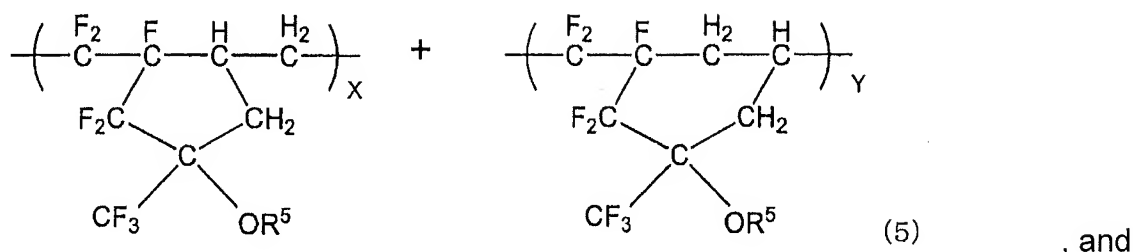


AMENDMENTS TO THE CLAIMS

1. (currently amended) A photoresist composition comprising:

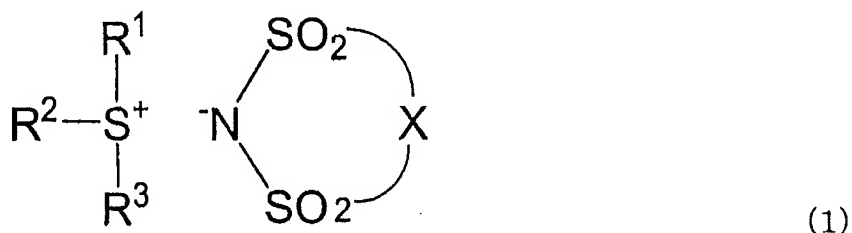
(A) a polymer component comprising an alkaline-soluble constitutional unit that contains an aliphatic cyclic group having both (i) a fluorine atom or a fluorinated alkyl group and (ii) an alcoholic hydroxide group, the alkaline solubility of the polymer component being changeable by action of an acid wherein said polymer component comprises at least one polymer selected from the group represented by the following Formulas:





combinations thereof; wherein in the Formulas (3), (4), and/or (5), Z represents an oxygen atom, an oxymethylene group (-O(CH₂)-), or a single bond; n' and m' are independently selected to be an integer of 1 to 5; R³ represents a hydrogen atom or methyl group; R⁴ is an acid-dissociative dissolution-controlling group; R⁵ represents a hydrogen atom or a C1 to C15 alkyloxymethyl group; and X and Y represent 10 to 50 mole %; and

(B) an acid generating component, capable of generating an acid by way of exposure, that contains at least a sulfonium compound expressed by the general formula (1) below:



wherein, in the formula (1), X represents a C2 to C6 alkylene group of which at least a hydrogen atom is substituted by fluorine atom; R¹ to R³ represent, independently of each other, an aryl or alkyl group; and at least one of R¹ to R³ represents an aryl group.

2. (original) A photoresist composition according to claim 1, further comprising a nitrogen-containing organic compound.

3. (original) A photoresist composition according to claim 1, further comprising an organic carboxylic acid, or a phosphorous oxo acid or derivative thereof.

4. (original) A method of forming a resist pattern, comprising:

coating the photoresist composition according to claim 1 on a substrate to form a resist film,

selectively exposing the resist film, and

heating and developing the resist film after exposure to form a resist pattern.

5. (original) A method of forming a resist pattern according to claim 4, wherein a SiON film is provided on the substrate.